

FEATURES

Complementary Type The NPN Transistor
MMBT3904 is Recommended
Epitaxial Planar Die Construction



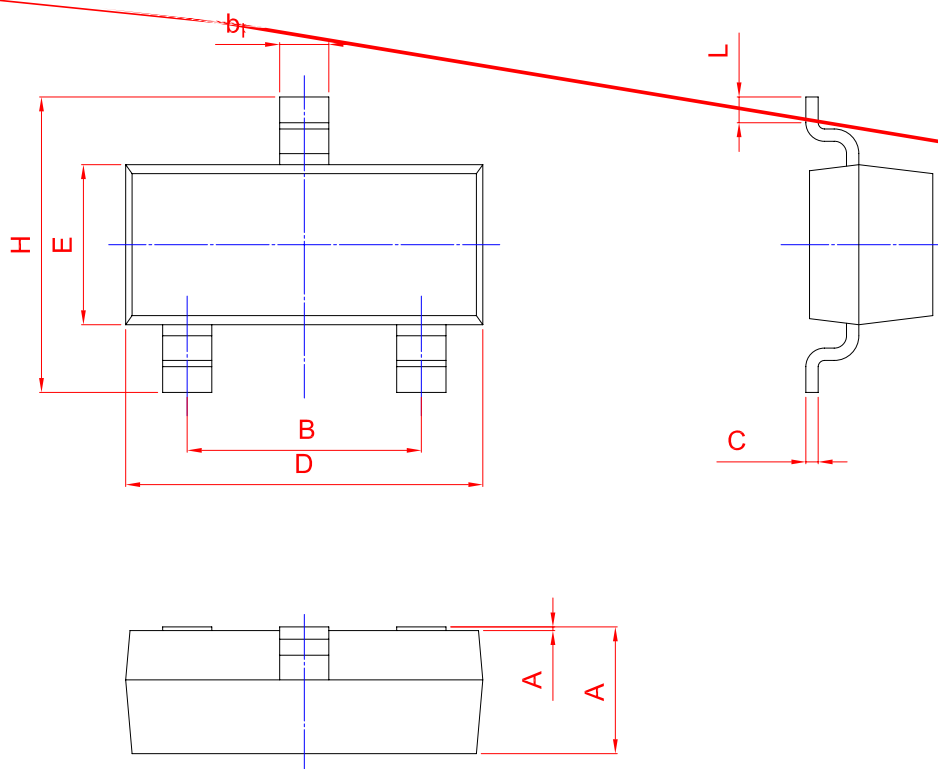
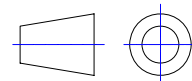
MARKING: 2A

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_{C}	Collector Current	-200	mA
P_{C}	Total Device Dissipation	200	mW
R_{JA}	Thermal Resistance Junction to Ambient	625	$^\circ\text{C}/\text{W}$
T_{J}	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55 ~ +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	$I_{\text{C}}=-10\mu\text{A}, I_{\text{E}}=0$	-40		V



UNIT	A		b_p	C	D	E	H_E	A_1	L_p
mm	1.40 0.95		0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20